

MOSFETs Silicon N-channel MOS (U-MOSVII-H)

XPN12006NC

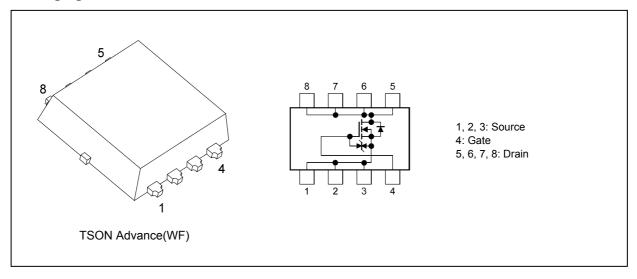
1. Applications

- · Automotive
- Switching Voltage Regulators
- · DC-DC Converters
- · Motor Drivers

2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 9.8 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (4) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (5) Enhancement mode: $V_{th} = 1.5 \text{ to } 2.5 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA})$

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Character | stics | | Symbol | Rating | Unit |
|--------------------------------|--------------------------|----------|------------------|------------|------|
| Drain-source voltage | | | V_{DSS} | 60 | V |
| Gate-source voltage | | | V _{GSS} | ±20 | |
| Drain current (DC) | | (Note 1) | I _D | 20 | Α |
| Drain current (pulsed) | | (Note 1) | I _{DP} | 60 | |
| Power dissipation | (T _c = 25 °C) | | P _D | 65 | W |
| Power dissipation | (t = 10 s) | (Note 2) | | 2.27 | |
| Power dissipation | (t = 10 s) | (Note 3) | | 0.84 | |
| Single-pulse avalanche energy | | (Note 4) | E _{AS} | 41 | mJ |
| Single-pulse avalanche current | | | I _{AS} | 20 | Α |
| Channel temperature | | (Note 5) | T _{ch} | 175 | °C |
| Storage temperature | | (Note 5) | T _{stg} | -55 to 175 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit | | |
|--------------------------------------|--------------------------|----------|-----------------------|-----|------|
| Channel-to-case thermal impedance | (T _c = 25 °C) | | Z _{th(ch-c)} | 2.3 | °C/W |
| Channel-to-ambient thermal impedance | (t = 10 s) | (Note 2) | Z _{th(ch-a)} | 66 | |
| Channel-to-ambient thermal impedance | (t = 10 s) | (Note 3) | Z _{th(ch-a)} | 178 | |

- Note 1: Ensure that the channel temperature does not exceed 175 °C.
- Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
- Note 4: V_{DD} = 48 V, T_{ch} = 25 °C (initial), L = 79.1 μ H, R_{G} = 25 Ω , I_{AS} = 20 A
- Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

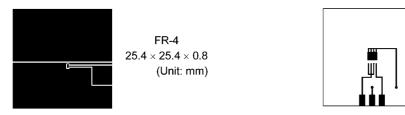


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

FR-4

 $25.4\times25.4\times0.8$

(Unit: mm)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±10 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 60 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 60 | _ | | V |
| | V _{(BR)DSX} | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 40 | _ | | |
| Gate threshold voltage | V_{th} | $V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$ | 1.5 | _ | 2.5 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 4.5 V, I _D = 10 A | _ | 14.8 | 23.7 | mΩ |
| | | V _{GS} = 10 V, I _D = 10 A | _ | 9.8 | 12.0 | |

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | _ | 1100 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 70 | _ | |
| Output capacitance | C _{oss} | | _ | 600 | | |
| Gate resistance | r _g | | | 2.0 | 4.0 | Ω |
| Switching time (rise time) | t _r | See Fig. 6.2.1 | | 5 | | ns |
| Switching time (turn-on time) | t _{on} | | | 15 | _ | ns |
| Switching time (fall time) | t _f | | _ | 8 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 33 | _ | ns |

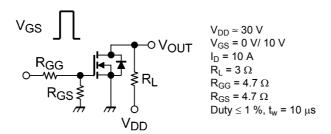


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Q_g | $V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$ | _ | 23 | 1 | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 6 | | |
| Gate-drain charge | Q_{gd} | | _ | 4 | _ | |

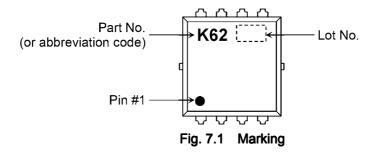
6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------------|----------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) (Not | (6) I _{DRP} | _ | _ | _ | 60 | Α |
| Diode forward voltage | V _{DSF} | I _{DR} = 20 A, V _{GS} = 0 V | _ | _ | -1.2 | V |

Note 6: Ensure that the channel temperature does not exceed 175 °C.



7. Marking





8. Characteristics Curves (Note)

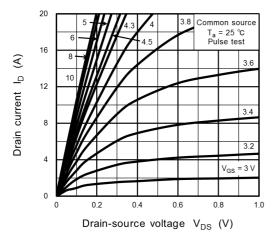


Fig. 8.1 I_D - V_{DS}

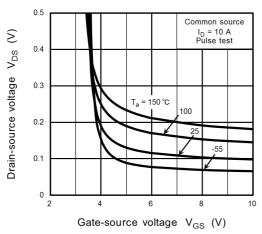


Fig. 8.3 V_{DS} - V_{GS}

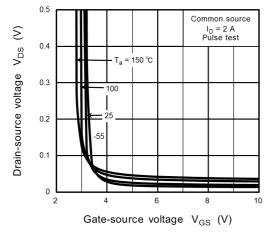


Fig. 8.5 V_{DS} - V_{GS}

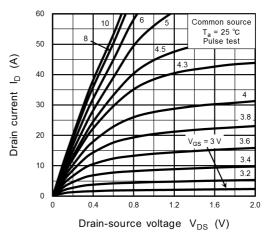


Fig. 8.2 I_D - V_{DS}

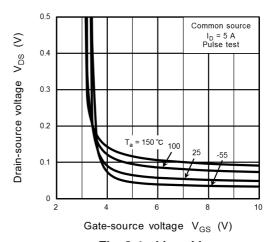


Fig. 8.4 V_{DS} - V_{GS}

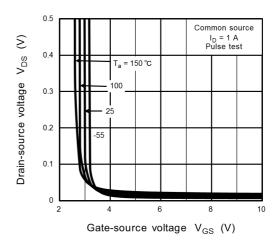


Fig. 8.6 $V_{DS} - V_{GS}$



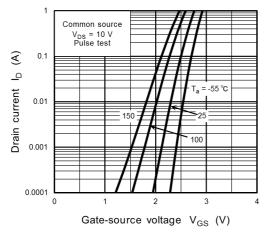


Fig. 8.7 I_D - V_{GS}

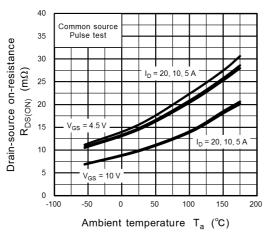


Fig. 8.9 R_{DS(ON)} - T_a

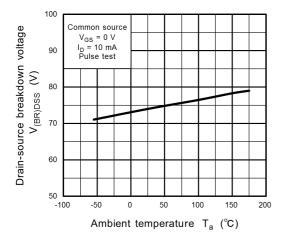


Fig. 8.11 V_{(BR)DSS} - T_a

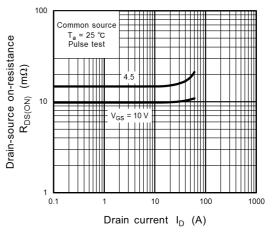


Fig. 8.8 R_{DS(ON)} - I_D

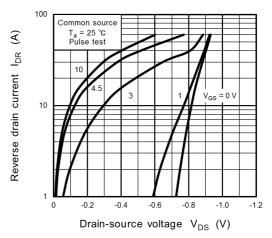


Fig. 8.10 I_{DR} - V_{DS}

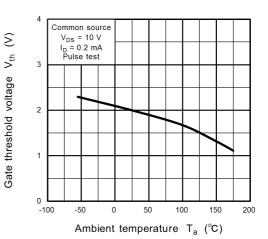


Fig. 8.12 Vth - Ta



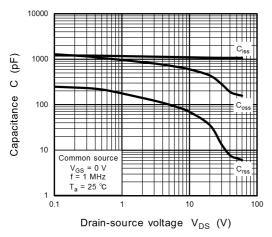


Fig. 8.13 Capacitance - V_{DS}

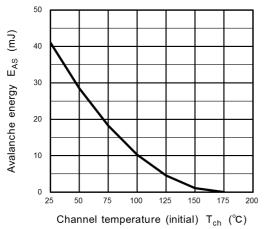


Fig. 8.15 EAS - Tch

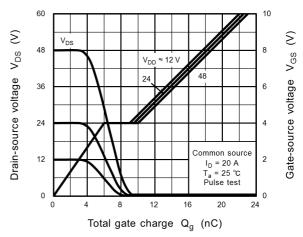


Fig. 8.14 Dynamic Input/Output Characteristics

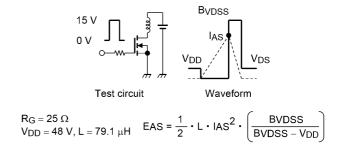


Fig. 8.16 Test Circuit/Waveform



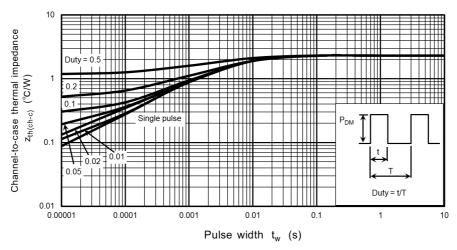
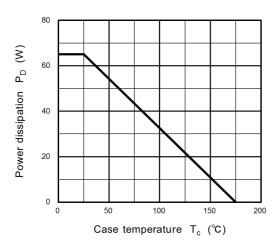


Fig. 8.17 $z_{th(ch-c)} - t_w$ (Guaranteed Maximum)



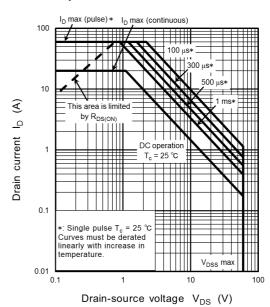


Fig. 8.18 P_D - T_c (Guaranteed Maximum)

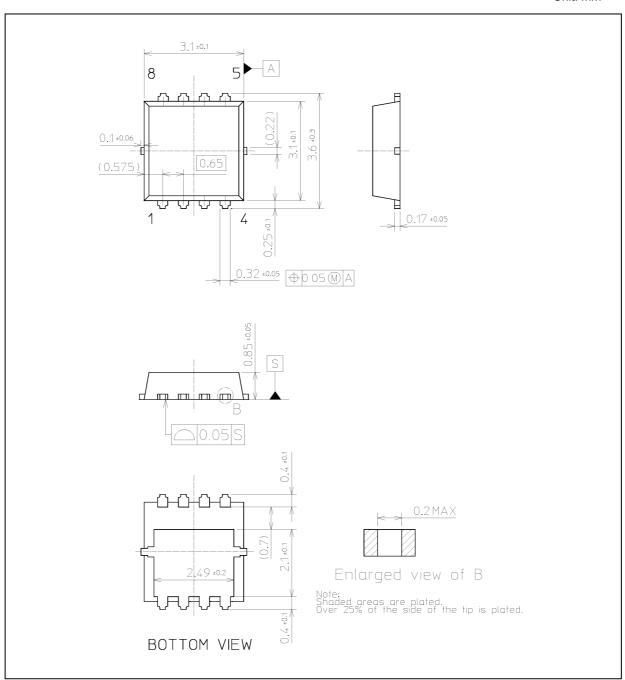
Fig. 8.19 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.026 g (typ.)

| Package Name(s) |
|----------------------------|
| TOSHIBA: 2-3X2A |
| Nickname: TSON Advance(WF) |



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